

DATA SHEET

74LVC10A

Triple 3-input NAND gate

Product specification

1998 Apr 28



Triple 3-input NAND gate

74LVC10A

FEATURES

- Wide supply voltage range of 1.2 V to 3.6 V
- In accordance with JEDEC standard no. 8-1A.
- Inputs accept voltages up to 5.5 V
- CMOS low power consumption
- Direct interface with TTL levels
- Output capability: standard
- I_{CC} category: SSI

DESCRIPTION

The 74LVC10A is a high performance, low power, low voltage, Si gate CMOS device and superior to most advanced CMOS compatible TTL families.

The 74LVC10A provides the 3-input NAND function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \leq 2.5$ ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	Propagation delay nA, nB, nC to nY	$C_L = 50$ pF; $V_{CC} = 3.3$ V	3.9	ns
C_I	Input capacitance		5.0	pF
C_{PD}	Power dissipation capacitance per gate	$V_I = GND$ to V_{CC}^1	26	pF

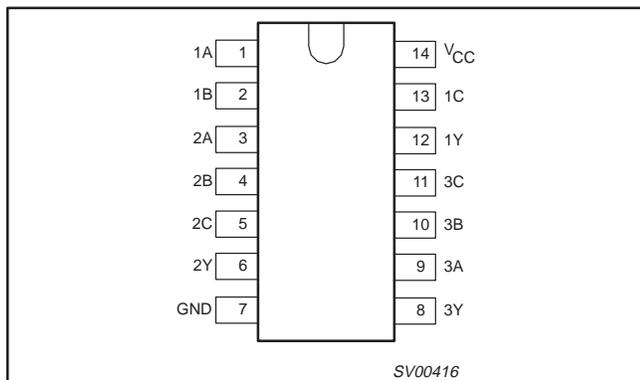
NOTE:

- C_{PD} is used to determine the dynamic power dissipation (P_D in μW)
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz; C_L = output load capacity in pF;
 f_o = output frequency in MHz; V_{CC} = supply voltage in V;
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

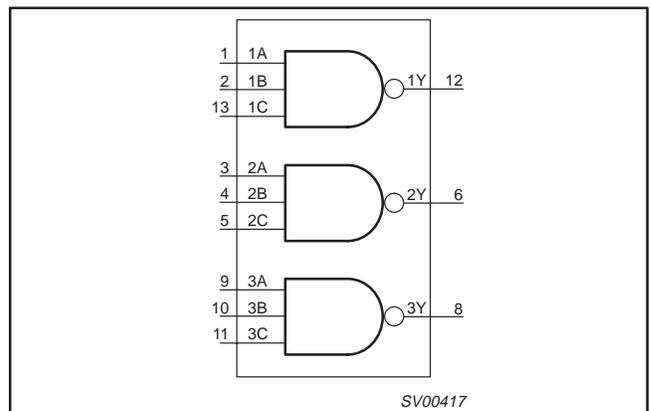
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic SO	-40°C to +85°C	74LVC10A D	74LVC10A D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74LVC10A DB	74LVC10A DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74LVC10A PW	74LVC10APW DH	SOT402-1

PIN CONFIGURATION



LOGIC SYMBOL



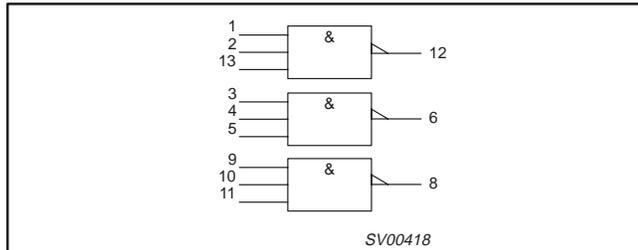
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A – 3A	Data inputs
2, 4, 10	1B – 3B	Data inputs
7	GND	Ground (0 V)
12, 6, 8	1Y – 3Y	Data outputs
13, 5, 11	1C – 3C	Data inputs
14	V_{CC}	Positive supply voltage

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LOGIC SYMBOL (IEEE/IEC)



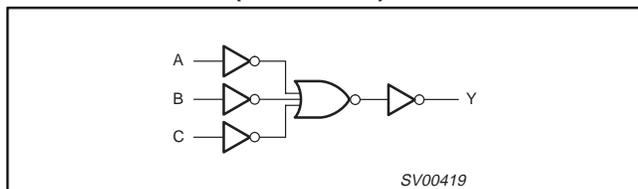
FUNCTION TABLE

INPUTS			OUTPUTS
nA	nB	nC	nY
L	L	L	H
L	L	H	H
L	H	L	H
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	L

NOTES:

H = HIGH voltage level
L = LOW voltage level

LOGIC DIAGRAM (ONE GATE)



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	LIMITS		UNIT
			MIN	MAX	
V_{CC}	DC supply voltage (for max. speed performance)		2.7	3.6	V
V_{CC}	DC supply voltage (for low-voltage applications)		1.2	3.6	V
V_I	DC input voltage range		0	5.5	V
T_{amb}	Operating free-air temperature range		-40	+85	°C
t_r, t_f	Input rise and fall times	$V_{CC} = 1.2$ to $2.7V$ $V_{CC} = 2.7$ to $3.6V$	0	20 10	ns/V

ABSOLUTE MAXIMUM RATINGS¹

In accordance with the Absolute Maximum Rating System (IEC 134).
Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		-0.5 to +6.5	V
I_{IK}	DC input diode current	$V_I < 0$	-50	mA
V_I	DC input voltage	Note 2	-0.5 to +6.5	V
I_{OK}	DC output diode current	$V_O > V_{CC}$ or $V_O < 0$	± 50	mA
$V_{I/O}$	DC output voltage; output HIGH or LOW	Note 2	-0.5 to $V_{CC} + 0.5$	V
	DC input voltage; output 3-State	Note 2	-0.5 to 6.5	
I_O	DC output source or sink current	$V_O = 0$ to V_{CC}	± 50	mA
I_{GND}, I_{CC}	DC V_{CC} or GND current		± 100	mA
T_{stg}	Storage temperature range		-65 to +150	°C
P_{TOT}	Power dissipation per package			
	- plastic mini-pack (SO) - plastic shrink mini-pack (SSOP and TSSOP)	above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	500 500	mW

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

Triple 3-input NAND gate

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DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			Temp = -40°C to +85°C			
			MIN	TYP ¹	MAX	
V _{IH}	HIGH level Input voltage	V _{CC} = 1.2V	V _{CC}			V
		V _{CC} = 2.7 to 3.6V	2.0			
V _{IL}	LOW level Input voltage	V _{CC} = 1.2V			GND	V
		V _{CC} = 2.7 to 3.6V			0.8	
V _{OH}	HIGH level output voltage	V _{CC} = 2.7V; V _I = V _{IH} or V _{IL} ; I _O = -12mA	V _{CC} - 0.5			V
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = -100µA	V _{CC} - 0.2	V _{CC}		
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = -12mA	V _{CC} - 0.6			
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = -24mA	V _{CC} - 1.0			
V _{OL}	LOW level output voltage	V _{CC} = 2.7V; V _I = V _{IH} or V _{IL} ; I _O = 12mA			0.40	V
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = 100µA			0.20	
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = 24mA			0.55	
I _I	Input leakage current	V _{CC} = 3.6V; V _I = 5.5V or GND		± 0.1	± 5	µA
I _{CC}	Quiescent supply current	V _{CC} = 3.6V; V _I = V _{CC} or GND; I _O = 0		0.1	10	µA
ΔI _{CC}	Additional quiescent supply current per input pin	V _{CC} = 2.7V to 3.6V; V _I = V _{CC} - 0.6V; I _O = 0		5	500	µA

NOTE:

1. All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

AC CHARACTERISTICS

GND = 0 V; t_r = t_f ≤ 2.5 ns; C_L = 50 pF

SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT
			V _{CC} = 3.3V ± 0.3V			V _{CC} = 2.7V		
			MIN	TYP ¹	MAX	MIN	MAX	
t _{PHL} / t _{PLH}	Propagation delay nA, nB, nC to nY	Figures 1, 2	1.5	3.9	5.7	1.5	6.7	ns

NOTE:

1. These typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

AC WAVEFORMS

V_M = 1.5 V at V_{CC} ≥ 2.7 V

V_M = 0.5 • V_{CC} at V_{CC} < 2.7 V

V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.

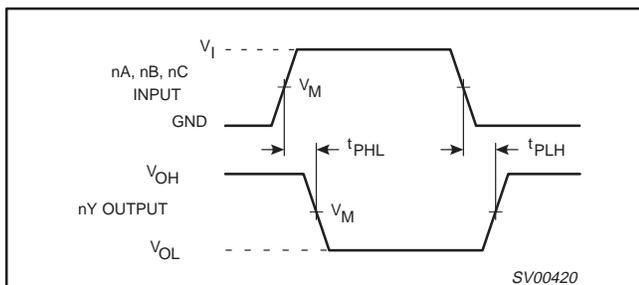


Figure 1. Input (nA, nB, nC) to output (nY) propagation delays.

TEST CIRCUIT

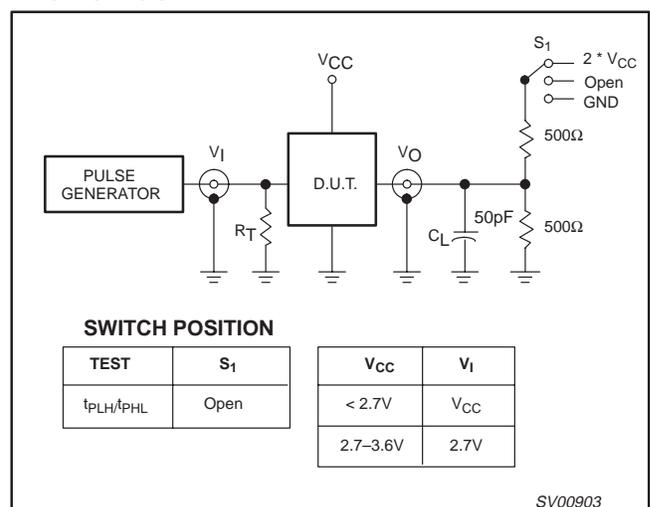


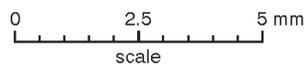
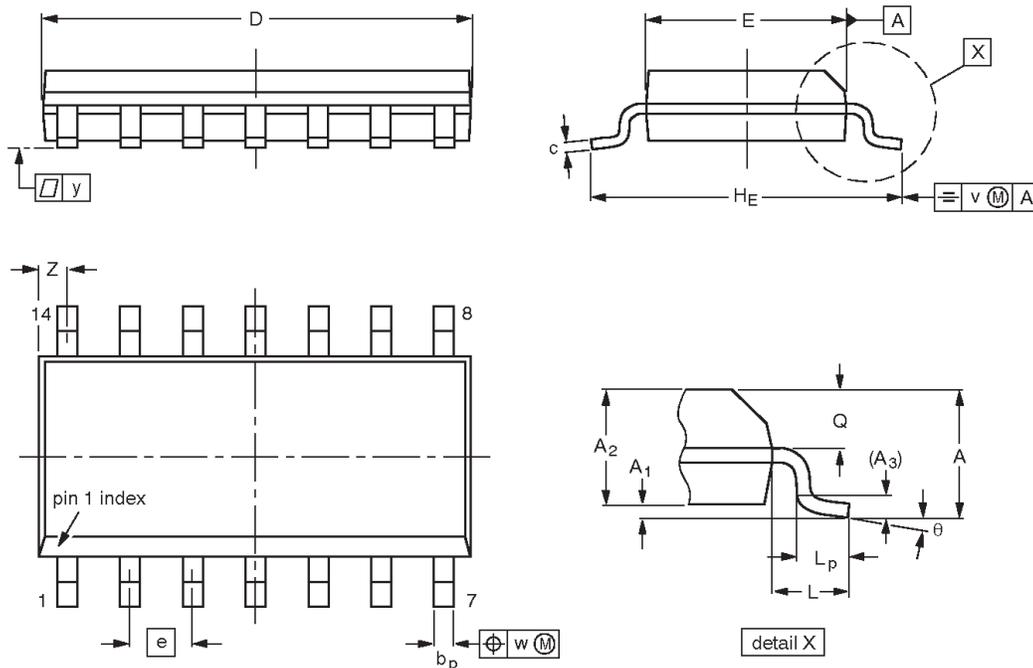
Figure 2. Load circuitry for switching times.

Triple 3-input NAND gate

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	HE	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

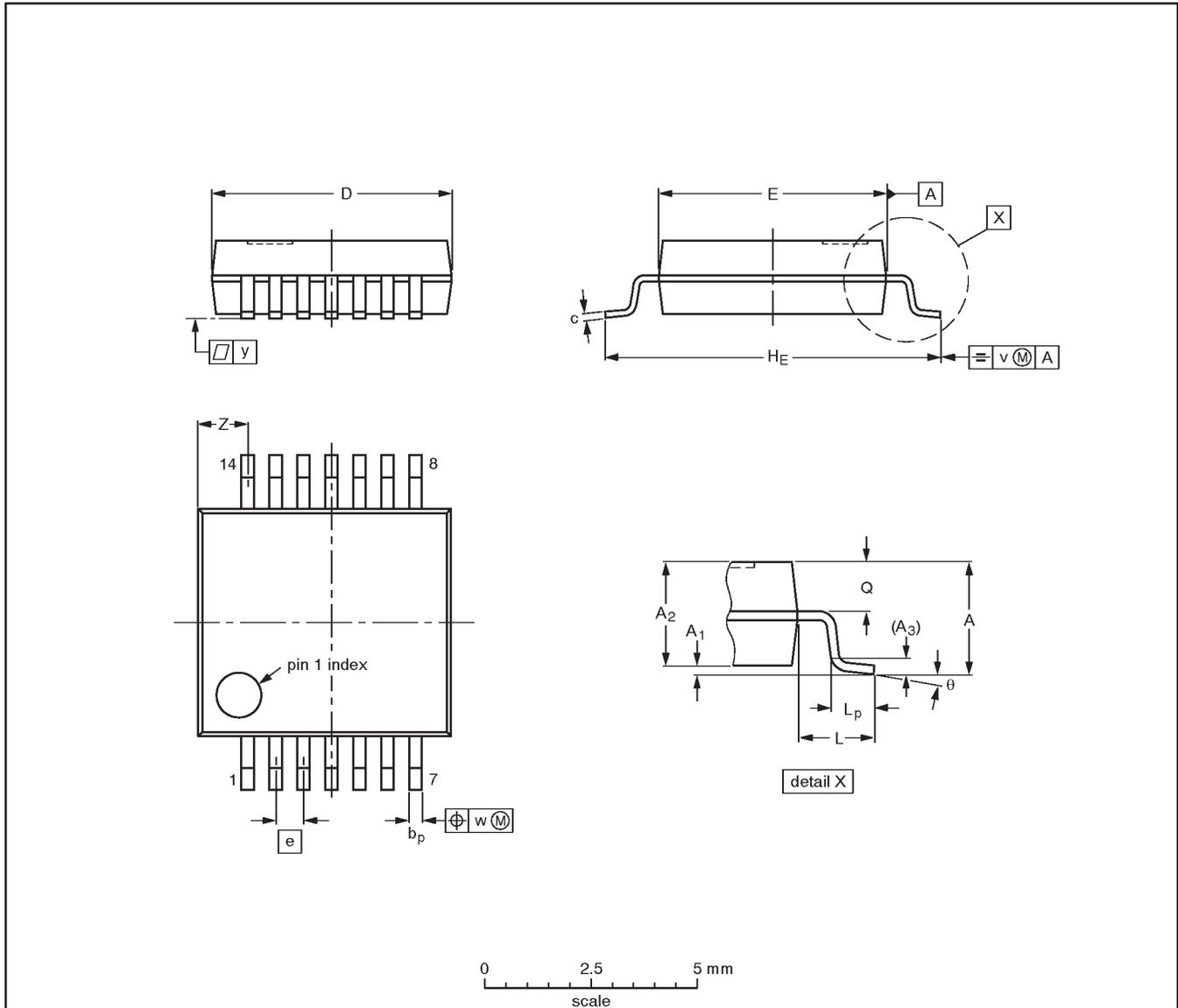
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT108-1	076E06S	MS-012AB				95-01-23 97-05-22

Triple 3-input NAND gate

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

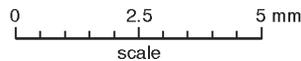
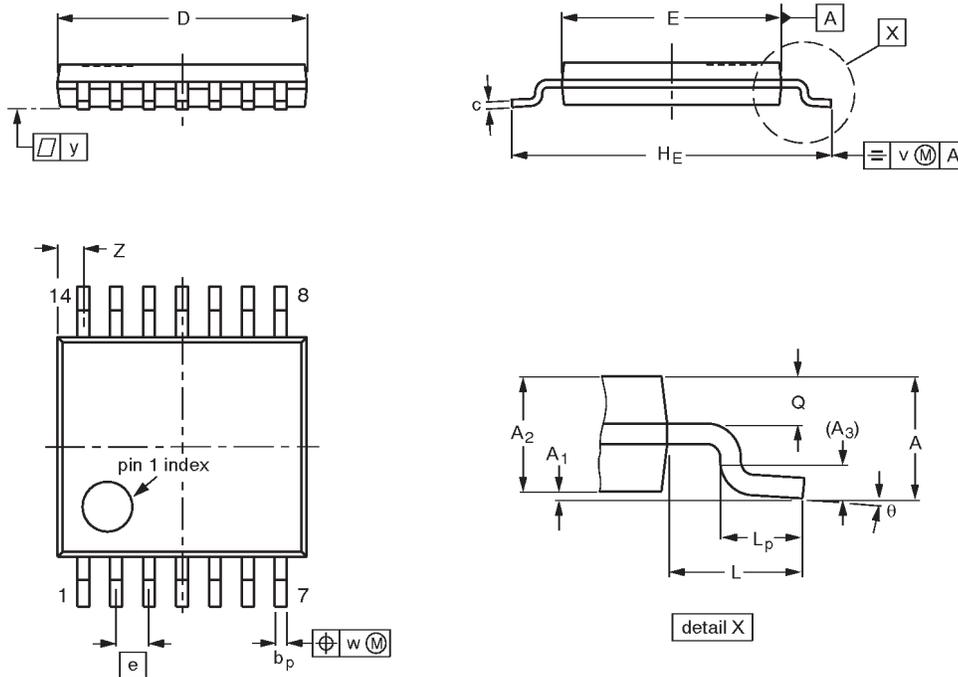
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT337-1		MO-150AB				95-02-04 96-01-18

Triple 3-input NAND gate

74LVC10A

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT402-1		MO-153				-94-07-12 95-04-04

Triple 3-input NAND gate

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Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
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[1] Please consult the most recently issued datasheet before initiating or completing a design.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Philips Semiconductors
811 East Arques Avenue
P.O. Box 3409
Sunnyvale, California 94088-3409
Telephone 800-234-7381

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